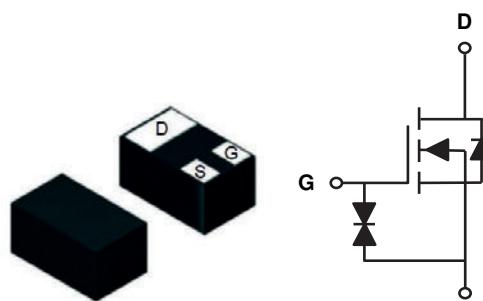


Main Product Characteristics

BV_{DSS}	30V
$R_{DS(ON)}$	160m Ω (Max.)
I_D	1.6A



DFN1006-3L
(SOT-883)

Schematic Diagram



Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery

Description

The GSFZ03016 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Maximum	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current @ $V_{GS}=4.5\text{V}$, $T_A=25^\circ\text{C}$	I_D	1.6	A
Continuous Drain Current @ $V_{GS}=4.5\text{V}$, $T_A=75^\circ\text{C}$		1.3	A
Pulsed Drain Current	I_{DM}	6.2	A
Total Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	0.97	mW
Thermal Resistance Junction to Ambient ¹	$R_{\theta JA}$	129	°C/W
Junction and Storage Temperature Range	T_J/T_{STG}	-55 to +150	°C

Note:

1. Device mounted on FR-4 substrate PC board, 2oz copper, with 1 inch square copper plate.

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
On / Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}, T_c=25^\circ\text{C}$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 8\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 10	μA
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	0.4	-	1.1	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=0.2\text{A}$	-	130	160	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=0.2\text{A}$	-	140	190	
		$V_{\text{GS}}=2.5\text{V}, I_{\text{D}}=0.1\text{A}$	-	160	215	
Dynamic and Switching Characteristics						
Input Capacitance	C_{iss}	$V_{\text{DS}}=15\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	134	-	pF
Output Capacitance	C_{oss}		-	12.8	-	
Reverse Transfer Capacitance	C_{rss}		-	6.9	-	
Total Gate Charge	Q_g	$V_{\text{GS}}=4.5\text{V}, V_{\text{DS}}=15\text{V}, I_{\text{D}}=1.3\text{A}$	-	1.36	-	nC
Gate Source Charge	Q_{gs}		-	0.18	-	
Gate Drain Charge	Q_{gd}		-	0.33	-	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{GS}}=4.5\text{V}, V_{\text{DD}}=15\text{V}, I_{\text{D}}=1.3\text{A}, R_{\text{GEN}}=4.5\Omega$	-	4.4	-	ns
Turn-on Rise Time	t_r		-	11.7	-	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		-	20.8	-	
Turn-off Fall Time	t_f		-	12.1	-	
Gate Resistance	R_g	$f=1\text{MHz}$	-	13	-	Ω
Source-Drain Ratings and Characteristics						
Maximum Body-Diode Continuous Current	I_S	-	-	-	1.6	A
Diode Forward Voltage	V_{SD}	$I_S=1.6\text{A}, V_{\text{GS}}=0\text{V}$	-	0.85	1.2	V

Typical Electrical and Thermal Characteristic Curves

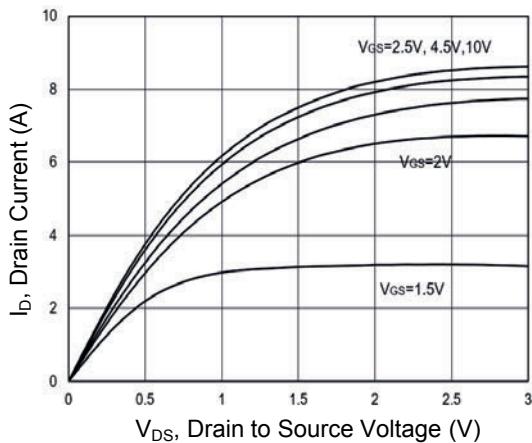


Figure 1. Output Characteristics

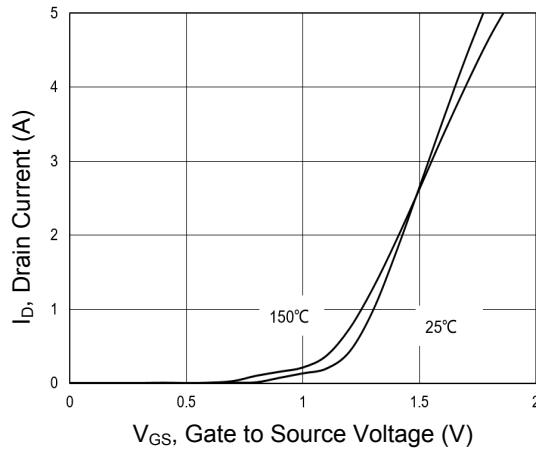


Figure 2. Transfer Characteristics

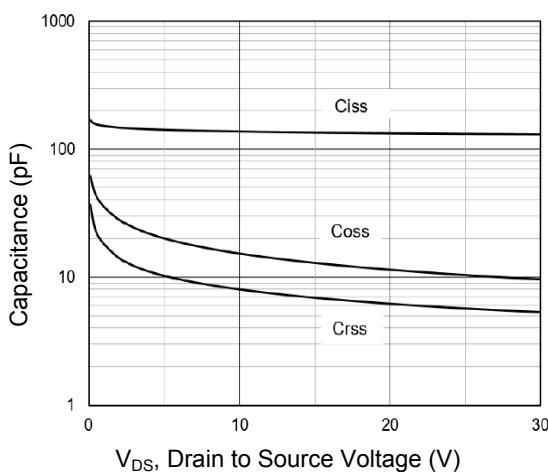


Figure 3. Capacitance Characteristics

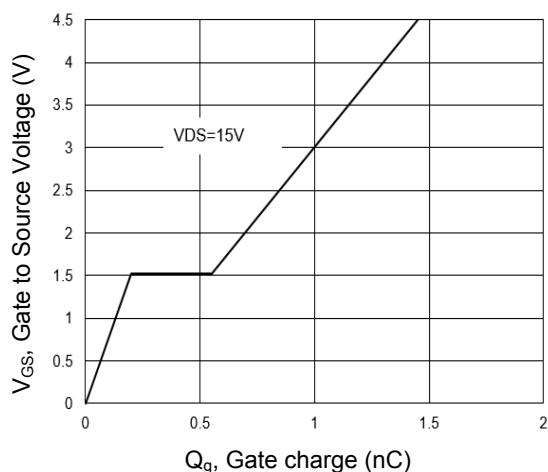


Figure 4. Gate Charge

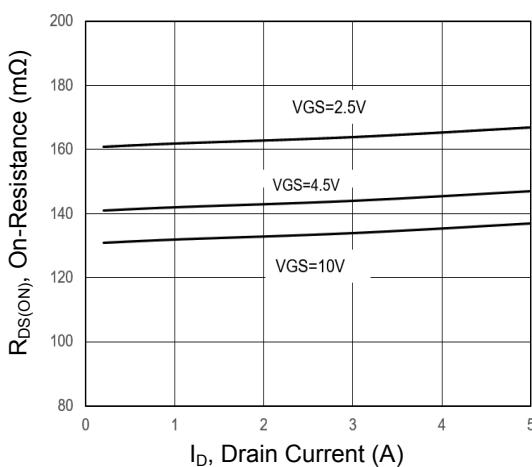


Figure 5. On-Resistance vs. Drain Current

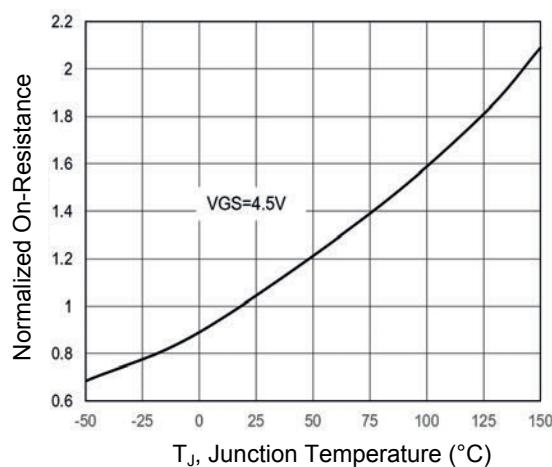


Figure 6. Normalized $R_{DS(on)}$ vs. T_J

Typical Electrical and Thermal Characteristic Curves

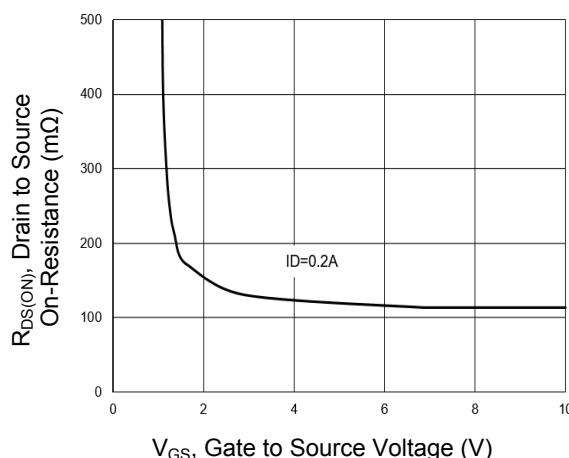


Figure 7. Typical R_{DSON} vs. Gate Voltage and Drain Current

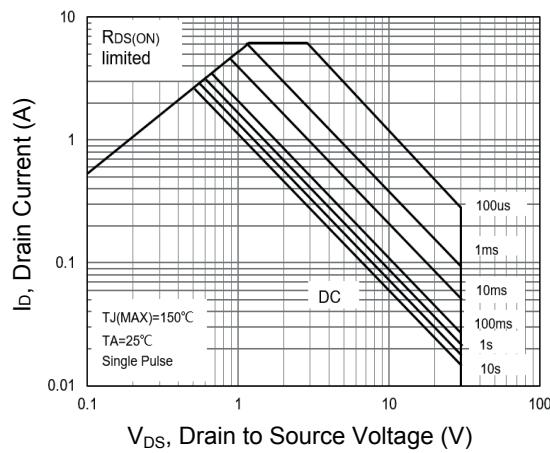


Figure 8. Safe Operation Area

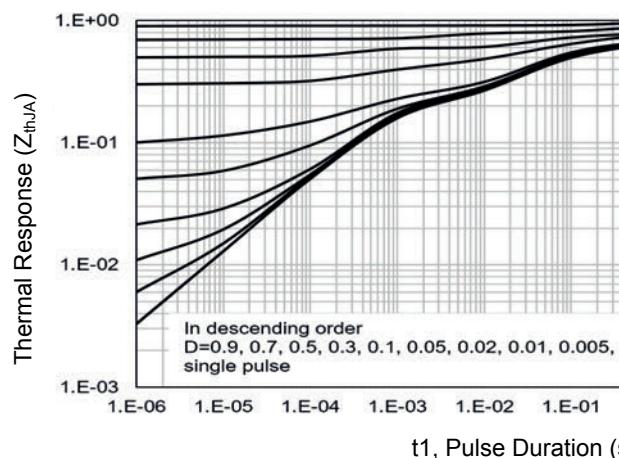
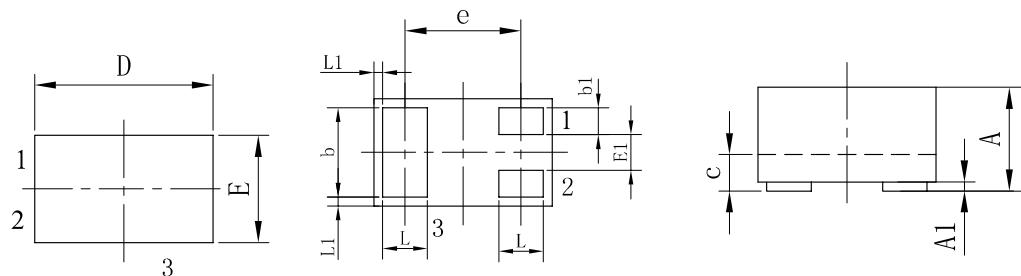


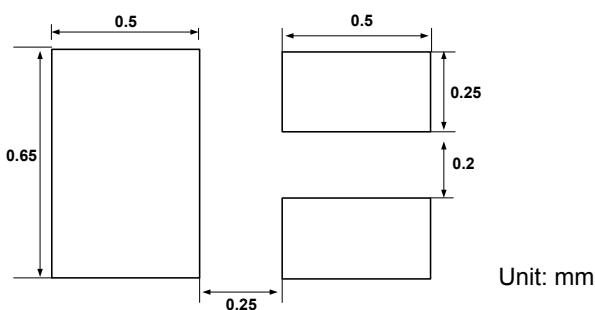
Figure 9. Maximum Effective Transient Thermal Impedance, Junction to Ambient

Package Outline Dimensions (DFN1006-3L/SOT-883)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.45	0.55	0.018	0.022
A1	0.00	0.05	0.000	0.002
b	0.45	0.55	0.018	0.022
b1	0.10	0.20	0.004	0.008
c	0.12	0.18	0.005	0.007
D	0.95	1.05	0.037	0.041
e	0.675 BSC		0.027 BSC	
E	0.55	0.65	0.022	0.026
E1	0.15	0.25	0.006	0.010
L	0.25	0.35	0.001	0.014
L1	0.05 REF		0.002 REF	

Recommended Pad Layout



Order Information

Device	Package	Marking	Carrier	Quantity
GSFZ03016	DFN1006-3L	U3	Tape & Reel	10,000 pcs / 7" Reel